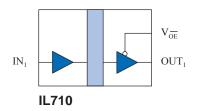


# High Speed/High Temperature Digital Isolators

#### **Functional Diagram**



Truth Table									
VI	V <sub>I</sub> V <sub>OE</sub> V <sub>O</sub>								
L	L	L							
Н	L	Н							
L	Н	Z							
Н	Н	Z							

#### **Features**

- +5 V/+3.3 V CMOS / TTL Compatible
- High Speed: 150 Mbps Typical (IL710S)
- High Temperature: -40°C to +125°C (IL710T)
- 2500 V<sub>RMS</sub> Isolation (1 min.)
- 300 ps Typical Pulse Width Distortion (IL710S)
- 4 ns Typical Propagation Delay Skew
- 10 ns Typical Propagation Delay
- 30 kV/µs Typical Common Mode Transient Immunity
- 8-pin MSOP, SOIC, and PDIP Packages
- UL1577 and IEC 61010-2001 Approval

#### **Applications**

- Digital Fieldbus
- RS-485 and RS-422
- Multiplexed Data Transmission
- Data Interfaces
- Board-to-Board Communication
- Digital Noise Reduction
- Operator Interface
- Ground Loop Elimination
- Peripheral Interfaces
- Serial Communication
- Logic Level Shifting

#### Description

NVE's IL700 family of high-speed digital isolators are CMOS devices manufactured with NVE's patented\* IsoLoop<sup>®</sup> spintronic Giant Magnetoresistive (GMR) technology. The IL710S is the world's fastest isolator of its type, with a 150 Mbps typical data rate.

The symmetric magnetic coupling barrier provides a typical propagation delay of only 10 ns and a pulse width distortion as low as 300 ps (0.3 ns), achieving the best specifications of any isolator. Typical transient immunity of 30 kV/ $\mu$ s is unsurpassed. The IL710 is ideal for isolating applications such as PROFIBUS, RS-485, and RS-422.

The IL710 is available in 8-pin MSOP, SOIC, and PDIP packages. Standard and S-Grade parts are specified over a temperature range of  $-40^{\circ}$ C to  $+100^{\circ}$ C; T-Grade parts are specified over a temperature range of  $-40^{\circ}$ C to  $+125^{\circ}$ C.



## Absolute Maximum Ratings

Parameters	Symbol	Min.	Тур.	Max.	Units	Test Conditions
Storage Temperature	Ts	-55		150	°C	
Ambient Operating Temperature <sup>(1)</sup> IL710T	T <sub>A</sub>	-55		125 135	°C	
Supply Voltage	$V_{DD1}, V_{DD2}$	-0.5		7	V	
Input Voltage	VI	-0.5		V <sub>DD1</sub> +0.5	V	
Input Voltage	$V_{\overline{OE}}$	-0.5		V <sub>DD2</sub> +0.5	V	
Output Voltage	Vo	-0.5		V <sub>DD2</sub> +0.5	V	
Output Current Drive	Io			10	mA	
Lead Solder Temperature				260	°C	10 sec.
ESD			2		kV	HBM

#### **Recommended Operating Conditions**

Parameters	Symbol	Min.	Тур.	Max.	Units	Test Conditions
Ambient Operating Temperature						
IL710 and IL710S	TA	-40		100	°C	
IL710T	T <sub>A</sub>	-40		125	°C	
Supply Voltage	$V_{DD1}, V_{DD2}$	3.0		5.5	V	
Logic High Input Voltage	V <sub>IH</sub>	2.4		V <sub>DD1</sub>	V	
Logic Low Input Voltage	V <sub>IL</sub>	0		0.8	V	
Input Signal Rise and Fall Times	$t_{IR}, t_{IF}$			1	μs	

#### **Insulation Specifications**

Parameters	Symbol	Min.	Тур.	Max.	Units	Test Conditions
Creepage Distance						
MSOP		3.01			mm	
SOIC		4.04			mm	
PDIP		7.04			mm	
Leakage Current			0.2		μΑ	240 V <sub>RMS</sub> , 60 Hz
Barrier Impedance			>10 <sup>14</sup>   3		$\Omega \parallel pF$	

#### **Package Characteristics**

Parameters	Symbol	Min.	Тур.	Max.	Units	Test Conditions
Capacitance (Input–Output) <sup>(5)</sup>	C <sub>I-O</sub>		1.1		pF	f = 1 MHz
Thermal Resistance						
MSOP	$\theta_{\rm JC}$		168		°C/W	Thermonounle et conter
SOIC	$\theta_{\rm JC}$		144		°C/W	<ul> <li>Thermocouple at center</li> <li>underside of package</li> </ul>
PDIP	$\theta_{\rm JC}$		54		°C/W	underside of package
Package Power Dissipation	$P_{PD}$			150	mW	$f = 1 \text{ MHz}, V_{DD} = 5 \text{ V}$

#### Safety and Approvals

IEC61010-1

TUV Certificate Numbers:

#### N1502812, N1502812-101

#### **Classification as Reinforced Insulation**

Model	Package	Pollution Degree	Material Group	Max. Working Voltage
IL710-1	MSOP	ĪI	III	150 V <sub>RMS</sub>
IL710-2	PDIP	II	III	300 V <sub>RMS</sub>
IL710-3	SOIC	II	III	150 V <sub>RMS</sub>

#### UL 1577

Component Recognition Program File Number: E207481 Rated  $2500V_{RMS}$  for 1 minute

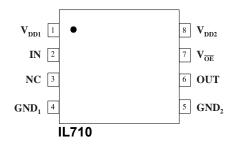
#### Soldering Profile

Per JEDEC J-STD-020C, MSL=2

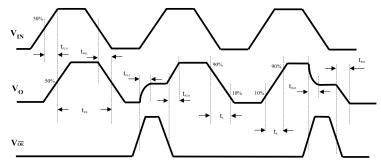


## IL710 Pin Connections

-	-	
1	V <sub>DD1</sub>	Supply voltage
2	IN	Data In
3	NC	No internal connection
4	GND <sub>1</sub>	Ground return for V <sub>DD1</sub>
5	GND <sub>2</sub>	Ground return for V <sub>DD2</sub>
6	OUT	Data Out
7	$V_{\overline{\text{OE}}}$	Output enable. Internally held low with 100 kΩ
8	V <sub>DD2</sub>	Supply voltage



## Timing Diagram



Legend	

t <sub>PLH</sub>	Propagation Delay, Low to High
t <sub>PHL</sub>	Propagation Delay, High to Low
t <sub>PW</sub>	Minimum Pulse Width
t <sub>PLZ</sub>	Propagation Delay, Low to High Impedance
t <sub>PZH</sub>	Propagation Delay, High Impedance to High
$t_{PHZ}$	Propagation Delay, High to High Impedance
$t_{PZL}$	Propagation Delay, High Impedance to Low
t <sub>R</sub>	Rise Time
t <sub>F</sub>	Fall Time



## 3.3 Volt Electrical Specifications

Electrical specifications are T<sub>min</sub> to T<sub>max</sub> unless otherwise stated.

Parameters	Symbol	Min.	Тур.	Max.	Units	Test Conditions
		DC Specific				• •
Input Quiescent Supply Current	I <sub>DD1</sub>		8	10	μΑ	
Output Quiescent Supply Current					•	
IL710 and IL710S	I <sub>DD2</sub>		1.7	2	mA	
IL710T			3.3	4		
Logic Input Current	II	-10		10	μΑ	
Logic High Output Voltage	V <sub>OH</sub>	V <sub>DD</sub> -0.1	V <sub>DD</sub>		v	$I_0 = -20 \ \mu A, \ V_I = V_{IH}$
Logie Ingli Output Voluge	• OH	$0.8 \text{ x V}_{\text{DD}}$	$0.9 \mathrm{x} \mathrm{V}_{\mathrm{DD}}$		·	$I_0 = -4 \text{ mA}, V_I = V_{IH}$
Logic Low Output Voltage	V <sub>OL</sub>		0	0.1	v	$I_0 = 20 \ \mu A, V_I = V_{IL}$
Logie Lott Output Foliage			0.5	0.8	·	$I_0 = 4 \text{ mA}, V_I = V_{IL}$
	S	Switching Spe	cifications			
Maximum Data Rate						
IL710 and IL710T		100	110		Mbps	$C_L = 15 \text{ pF}$
IL7108		130	140		Mbps	$C_L = 15 \text{ pF}$
Pulse Width <sup>(7)</sup>	PW	10	7.5		ns	50% Points, Vo
Propagation Delay Input to Output	t <sub>PHL</sub>		12	18	ns	$C_{L} = 15 \text{ pF}$
(High to Low)	-1 IIL			-	~	
Propagation Delay Input to Output	t <sub>PLH</sub>		12	18	ns	$C_L = 15 \text{ pF}$
(Low to High)	TEIT					
Propagation Delay Enable to Output	$t_{PHZ}$		3	5	ns	$C_{L} = 15 \text{ pF}$
(High to High Impedance)						
Propagation Delay Enable to Output	$t_{PLZ}$		3	5	ns	$C_{L} = 15 \text{ pF}$
(Low to High Impedance)						- *
Propagation Delay Enable to Output	t <sub>PZH</sub>		3	5	ns	$C_L = 15 \text{ pF}$
(High Impedance to High)						
Propagation Delay Enable to Output	$t_{PZL}$		3	5	ns	$C_L = 15 \text{ pF}$
(High Impedance to Low)						
Pulse Width Distortion <sup>(2)</sup>	DWD		2	2		$C = 15 \pi E$
IL710 and IL710T IL710S	PWD		2 1	33	ns	$C_L = 15 \text{ pF}$
Propagation Delay Skew <sup>(3)</sup>	+		4	6	na	$C_{L} = 15 \text{ pF}$
Output Rise Time (10%–90%)	t <sub>PSK</sub>		2	4	ns	$C_L = 15 \text{ pF}$ $C_L = 15 \text{ pF}$
Output Kise Time (10%–90%) Output Fall Time (10%–90%)	t <sub>R</sub>		2	4	ns ns	$C_L = 15 \text{ pF}$ $C_L = 15 \text{ pF}$
Common Mode Transient Immunity	t <sub>F</sub>			4		
(Output Logic High or Logic Low) <sup>(4)</sup>	$ CM_H , CM_L $	20	30		kV/μs	$V_{CM} = 300 V$
Dynamic Power Consumption <sup>(6)</sup>			140	240	µA/MHz	



## 5 Volt Electrical Specifications

Electrical	specifications	are	T <sub>min</sub> to	T <sub>max</sub>	unless	otherwise	stated.

Parameters	Symbol	Min.	Typ.	Max.	Units	Test Conditions
	• •	DC Specific	cations	•		• •
Input Quiescent Supply Current	I <sub>DD1</sub>		10	15	μΑ	
Output Quiescent Supply Current						
IL710 and IL710S	I <sub>DD2</sub>		2.5	3	mA	
IL710T			5	6		
Logic Input Current	I <sub>I</sub>	-10		10	μΑ	
Logic High Output Voltage	V <sub>OH</sub>	V <sub>DD</sub> -0.1	V <sub>DD</sub>		v	$I_0 = -20 \ \mu A, V_I = V_{IH}$
Logie High Output Voluge	• OH	0.8 x V <sub>DD</sub>	0.9 x V <sub>DD</sub>		•	$I_0 = -4 \text{ mA}, V_I = V_{IH}$
Logic Low Output Voltage	V <sub>OL</sub>		0	0.1	V	$I_0 = 20 \ \mu A, V_I = V_{IL}$
Logie Low Output Voltage	• OL		0.5	0.8		$I_0 = 4 \text{ mA}, V_I = V_{IL}$
	Ś	Switching Spe	cifications			
Maximum Data Rate						
IL710 and IL710T		100	110		Mbps	$C_L = 15 \text{ pF}$
IL710S		130	150		Mbps	$C_L = 15 \text{ pF}$
Pulse Width <sup>(7)</sup>	PW	10	7.5		ns	50% Points, Vo
Propagation Delay Input to Output	t <sub>PHL</sub>		10	15	ns	$C_{L} = 15 \text{ pF}$
(High to Low)	PHL		10	15	115	
Propagation Delay Input to Output	t <sub>PLH</sub>		10	15	ns	$C_{L} = 15 \text{ pF}$
(Low to High)	PLH		10	10	115	CL 10 pr
Propagation Delay Enable to Output	t <sub>PHZ</sub>		3	5	ns	$C_{L} = 15 \text{ pF}$
(High to High Impedance)	THZ				110	
Propagation Delay Enable to Output	$t_{PLZ}$		3	5	ns	$C_{L} = 15 \text{ pF}$
(Low to High Impedance)	TLZ				110	
Propagation Delay Enable to Output	t <sub>PZH</sub>		3	5	ns	$C_{L} = 15 \text{ pF}$
(High Impedance to High)	1211		_	_		
Propagation Delay Enable to Output	t <sub>PZL</sub>		3	5	ns	$C_{L} = 15 \text{ pF}$
(High Impedance to Low)	-1 ZL		_	_		
Pulse Width Distortion <sup>(2)</sup>						
IL710 and IL710T	PWD		2	3	ns	$C_L = 15 \text{ pF}$
IL710S			0.3	3		
Propagation Delay Skew <sup>(3)</sup>	t <sub>PSK</sub>		4	6	ns	$C_L = 15 \text{ pF}$
Output Rise Time (10%–90%)	t <sub>R</sub>		1	3	ns	$C_L = 15 \text{ pF}$
Output Fall Time (10%–90%)	t <sub>F</sub>		1	3	ns	$C_L = 15 \text{ pF}$
Common Mode Transient Immunity	$ CM_{H} ,  CM_{L} $	20	30		kV/μs	$V_{cm} = 300 V$
(Output Logic High or Logic Low) <sup>(4)</sup>	1 - 11 2  - "L	-				viii
Dynamic Power Consumption <sup>(6)</sup>			200	340	µA/MHz	

#### Notes (apply to both 3.3 V and 5 V specifications):

- 1. Absolute maximum ambient operating temperature means the device will not be damaged if operated under these conditions. It does not guarantee performance.
- 2. PWD is defined as  $|t_{PHL} t_{PLH}|$ . %PWD is equal to PWD divided by pulse width.
- 3.  $t_{PSK}$  is the magnitude of the worst-case difference in  $t_{PHL}$  and/or  $t_{PLH}$  between devices at 25°C.
- 4.  $CM_{H}$  is the maximum common mode voltage slew rate that can be sustained while maintaining  $V_0 > 0.8 V_{DD2}$ .  $CM_L$  is the maximum common mode input voltage that can be sustained while maintaining  $V_0 < 0.8 V$ . The common mode voltage slew rates apply to both rising and falling common mode voltage edges.
- 5. Device is considered a two terminal device: pins 1–4 shorted and pins 5–8 shorted.
- 6. Dynamic power consumption is calculated per channel and is supplied by the channel's input side power supply.
- 7. Minimum pulse width is the minimum value at which specified PWD is guaranteed.

#### Electrostatic Discharge Sensitivity

This product has been tested for electrostatic sensitivity to the limits stated in the specifications. However, NVE recommends that all integrated circuits be handled with appropriate care to avoid damage. Damage caused by inappropriate handling or storage could range from performance degradation to complete failure.



## **Application Information**

#### **Dynamic Power Consumption**

IsoLoop Isolators achieve their low power consumption from the way they transmit data across the isolation barrier. By detecting the edge transitions of the input logic signal and converting these to narrow current pulses, a magnetic field is created around the GMR Wheatstone bridge. Depending on the direction of the magnetic field, the bridge causes the output comparator to switch following the input logic signal. Since the current pulses are narrow, about 2.5 ns, the power consumption is independent of mark-to-space ratio and solely dependent on frequency. This has obvious advantages over optocouplers, which have power consumption heavily dependent on mark-to-space ratio.

#### **Power Supply Decoupling**

Both power supplies to these devices should be decoupled with low ESR 47 nF ceramic capacitors. Ground planes for both  $GND_1$  and  $GND_2$  are highly recommended for data rates above 10 Mbps. Capacitors must be located as close as possible to the  $V_{DD}$  pins.

### Signal Status on Start-up and Shut Down

To minimize power dissipation, input signals are differentiated and then latched on the output side of the isolation barrier to reconstruct the signal. This could result in an ambiguous output state depending on power up, shutdown and power loss sequencing. Therefore, the designer should consider including an initialization signal in the start-up circuit. Initialization consists of toggling the input either high then low, or low then high.

#### **Data Transmission Rates**

The reliability of a transmission system is directly related to the accuracy and quality of the transmitted digital information. For a digital system, those parameters which determine the limits of the data transmission are pulse width distortion and propagation delay skew.

Propagation delay is the time taken for the signal to travel through the device. This is usually different when sending a low-to-high than when sending a high-to-low signal. This difference, or error, is called pulse width distortion (PWD) and is usually in nanoseconds. It may also be expressed as a percentage:

 $PWD\% = \frac{Maximum Pulse Width Distortion (ns)}{Signal Pulse Width (ns)} \times 100\%$ 

For example, with data rates of 12.5 Mbps:

$$PWD\% = \frac{3 \text{ ns}}{80 \text{ ns}} \times 100\% = 3.75\%$$

This figure is almost **three times** better than any available optocoupler with the same temperature range, and **two times** better than any optocoupler regardless of published temperature range. IsoLoop isolators exceed the 10% maximum PWD recommended by PROFIBUS, and will run to nearly 35 Mb within the 10% limit.

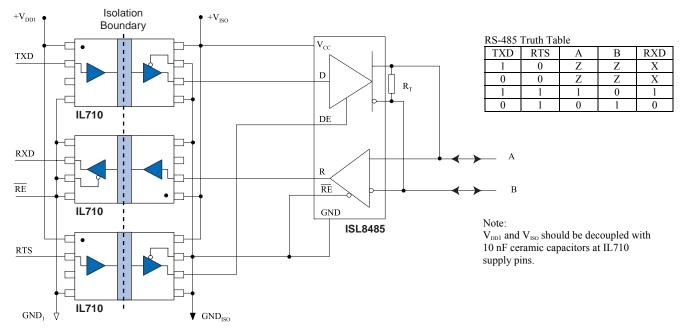
IL71(

Propagation delay skew is the signal propagation difference between two or more channels. This becomes significant in clocked systems because it is undesirable for the clock pulse to arrive before the data has settled. Short propagation delay skew is therefore especially critical in high data rate parallel systems for establishing and maintaining accuracy and repeatability. IL700 isolators have a maximum propagation delay skew of 6 ns, which is **five times** better than any optocoupler.



## **Application Diagrams**

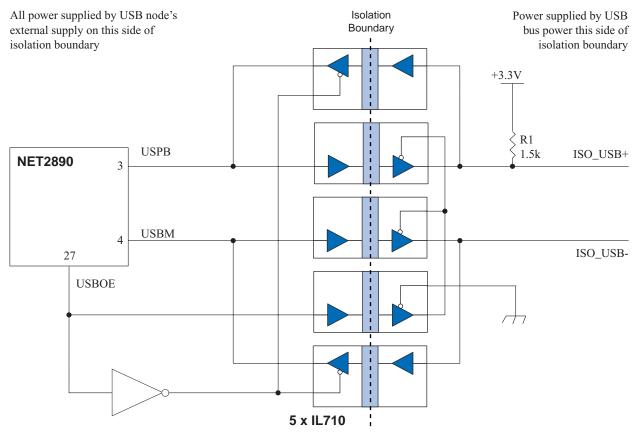
#### Isolated PROFIBUS / RS-485



NVE offers a unique line of PROFIBUS/RS-485 transceivers, but IL710 isolators can also be used as part of multi-chip designs using nonisolated PROFIBUS transceivers.



#### **Isolated USB**

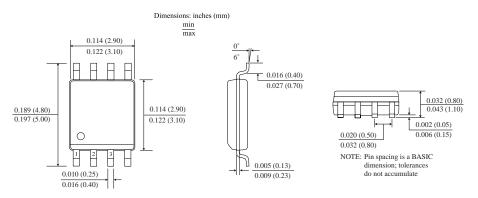


In this circuit, power is supplied by USB bus power on one side of the isolation barrier, and the USB node's external supply on the other side of the barrier. IL700 Isolators are specified with just 3 ns worst-case pulse width distortion.

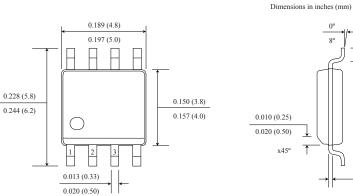


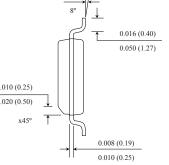
#### Package Drawings, Dimensions and Specifications

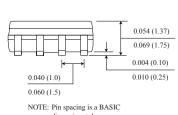
#### 8-pin MSOP



## 8-pin SOIC Package

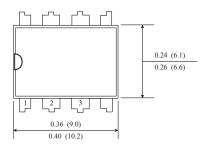


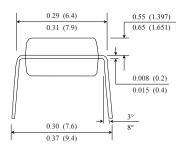


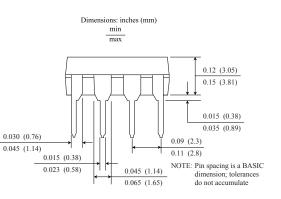


dimension; tolerances do not accumulate

#### 8-pin PDIP

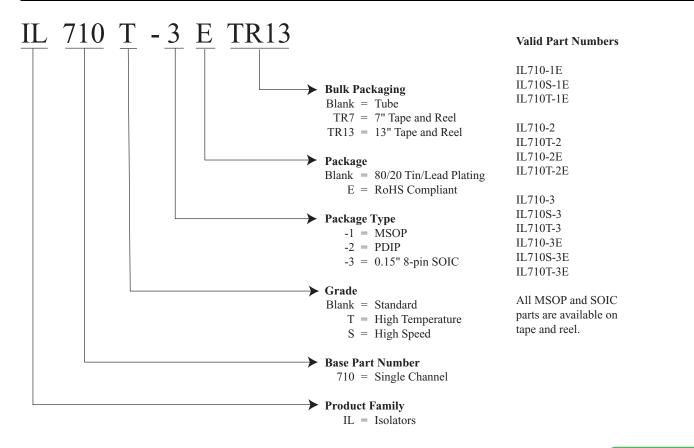








**Ordering Information and Valid Part Numbers** 



**RoHS** COMPLIANT



ISB-DS-001-IL710-R October 2008	<ul><li>Changes</li><li>IEC 61010 approval for MSOP version.</li></ul>
ISB-DS-001-IL710-Q	<ul><li>Changes</li><li>Added magnetic immunity to 3.3 and 5 volt electrical specifications.</li></ul>
	• Added diagram showing cross-axis direction.
	• Added magnetic compatibility to the applications information section.
ISB-DS-001-IL710-P	<ul> <li>Changes</li> <li>Note on all package drawings that pin-spacing tolerances are non-accumulating; change MSOP pin-spacing dimensions and tolerance accordingly.</li> </ul>
ISB-DS-001-IL710-O	<ul><li>Changes</li><li>Corrected PWD spec. on Isolated USB application diagram (p. 8).</li></ul>
	• Changed lower limit of length on PDIP package drawing and tightened pin-spacing tolerance on MSOP package drawing (p. 9).
ISB-DS-001-IL710-N	<ul><li>Changes</li><li>Changed IL710T output quiescent supply current specifications.</li></ul>
ISB-DS-001-IL710-M	<ul><li>Changes</li><li>Changed ordering information to reflect that devices are now fully RoHS compliant with no exemptions.</li></ul>
ISB-DS-001-IL710-L	<ul><li>Changes</li><li>Eliminated soldering profile chart</li></ul>
ISB-DS-001-IL710-K	<ul><li>Changes</li><li>Edited Profibus application</li></ul>
ISB-DS-001-IL710-J	<ul><li>Changes</li><li>MSOP package, S- and T-Grades added</li></ul>
	• Order information updated
ISB-DS-001-IL710-I	<ul><li>Changes</li><li>Added MSOP specifications</li></ul>
	• Updated UL and IEC numbers
ISB-DS-001-IL710-H	<ul><li>Changes</li><li>Revision letter added.</li></ul>
	• Storage temperature changed from 175°C max. to 150°C max.
	• Lead soldering temperature changed from 180°C max. to 260°C max.
	• Package Power Dissipation: Test Condition added: $f = 1 MHz$ , $V_{DD} = 5V$ .
	• IEC 61010-1 Classification: "Reinforced Insulation" added.
	• USB application circuit added.
	• Ordering Information: 5 Volt only option removed. Valid Part Numbers IL710-2B, IL710-3B, IL710-2BE, and IL710-3BE removed.



## About NVE

An ISO 9001 Certified Company

NVE Corporation manufactures innovative products based on unique spintronic Giant Magnetoresistive (GMR) technology. Products include Magnetic Field Sensors, Magnetic Field Gradient Sensors (Gradiometers), Digital Magnetic Field Sensors, Digital Signal Isolators, and Isolated Bus Transceivers.

NVE pioneered spintronics and in 1994 introduced the world's first products using GMR material, a line of ultra-precise magnetic sensors for position, magnetic media, gear speed and current sensing.

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#### Specifications are subject to change without notice.

ISB-DS-001-IL710-R October 2008